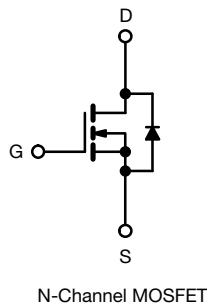


## E Series Power MOSFET

Thin-Lead TO-220 FULLPAK



### FEATURES

- Low figure-of-merit (FOM)  $R_{DS(on)} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

### PRODUCT SUMMARY

|                                         |                 |      |
|-----------------------------------------|-----------------|------|
| $V_{DS}$ (V) at $T_J$ max.              | 850             |      |
| $R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C | $V_{GS} = 10$ V | 0.38 |
| $Q_g$ max. (nC)                         | 88              |      |
| $Q_{gs}$ (nC)                           | 9               |      |
| $Q_{gd}$ (nC)                           | 16              |      |
| Configuration                           | Single          |      |

### ORDERING INFORMATION

|                                 |                          |
|---------------------------------|--------------------------|
| Package                         | Thin-lead TO-220 FULLPAK |
| Lead (Pb)-free and halogen-free | SiHA11N80E-GE3           |

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| PARAMETER                                                 | SYMBOL           | LIMIT          | UNIT |
|-----------------------------------------------------------|------------------|----------------|------|
| Drain-source voltage                                      | $V_{DS}$         | 800            | V    |
| Gate-source voltage                                       | $V_{GS}$         | $\pm 30$       |      |
| Continuous drain current ( $T_J = 150$ °C) <sup>a</sup>   | $V_{GS}$ at 10 V | $T_C = 25$ °C  | A    |
|                                                           |                  | $T_C = 100$ °C |      |
| Pulsed drain current <sup>b</sup>                         | $I_{DM}$         | 32             |      |
| Linear derating factor                                    |                  | 0.27           | W/°C |
| Single pulse avalanche energy <sup>c</sup>                | $E_{AS}$         | 226            | mJ   |
| Maximum power dissipation                                 | $P_D$            | 34             | W    |
| Operating junction and storage temperature range          | $T_J, T_{stg}$   | -55 to +150    | °C   |
| Drain-source voltage slope                                | $dv/dt$          | $T_J = 125$ °C | V/ns |
| Reverse diode $dv/dt$ <sup>d</sup>                        |                  |                |      |
| Soldering recommendations (peak temperature) <sup>e</sup> |                  | For 10 s       | °C   |
| Mounting torque                                           |                  | M3 screw       | Nm   |

#### Notes

- Limited by maximum junction temperature
- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 140$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 4.0$  A
- $I_{SD} \leq I_D$ ,  $di/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C
- 1.6 mm from case

**THERMAL RESISTANCE RATINGS**

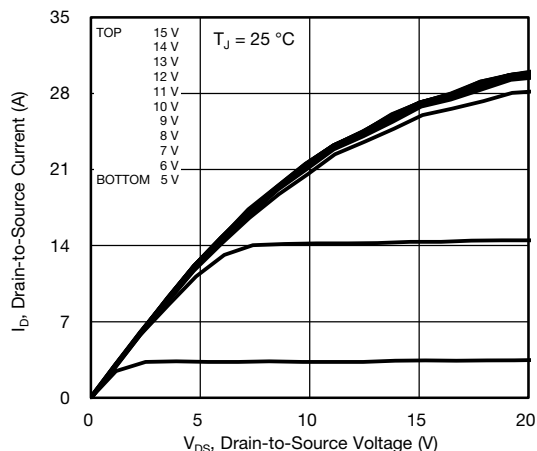
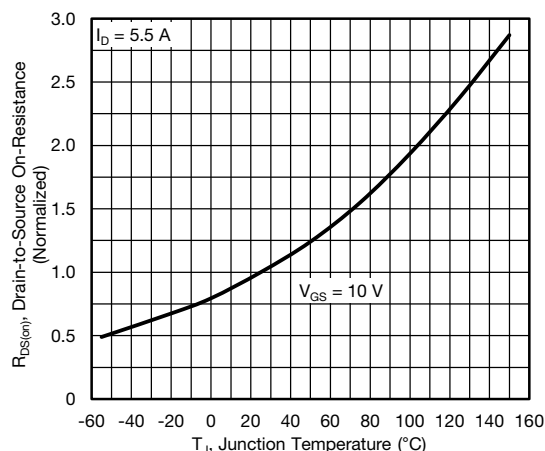
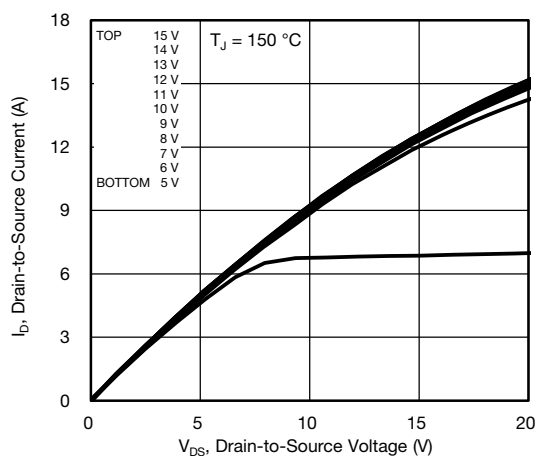
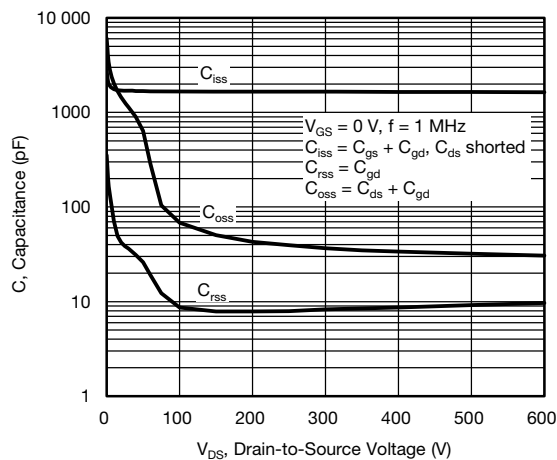
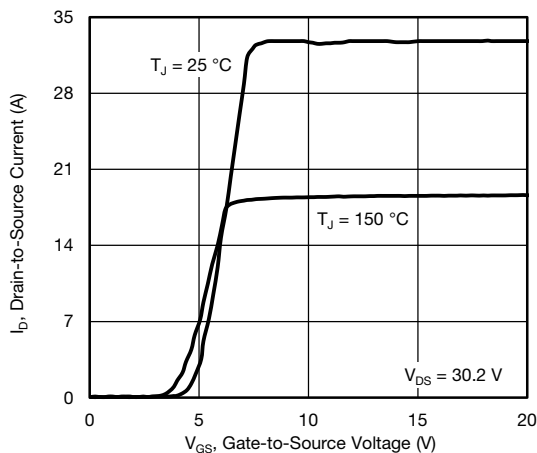
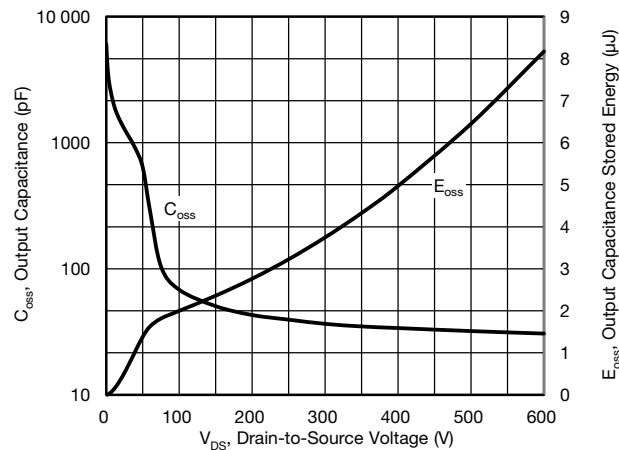
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum junction-to-ambient      | $R_{thJA}$ | -    | 65   | °C/W |
| Maximum junction-to-case (drain) | $R_{thJC}$ | -    | 3.7  |      |

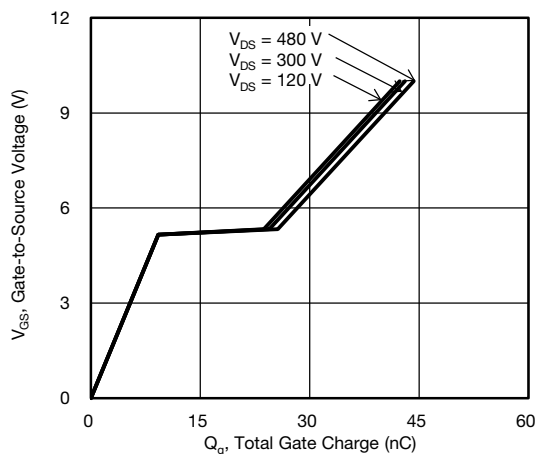
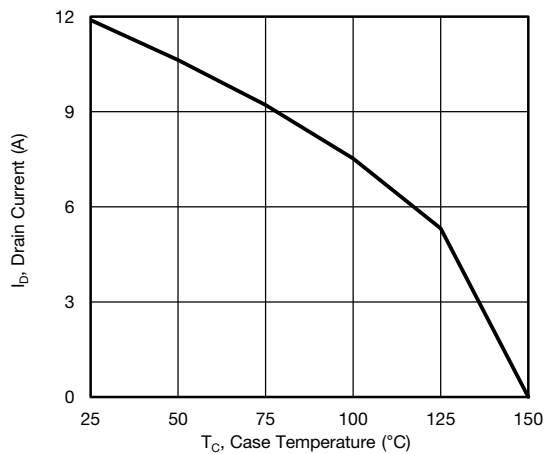
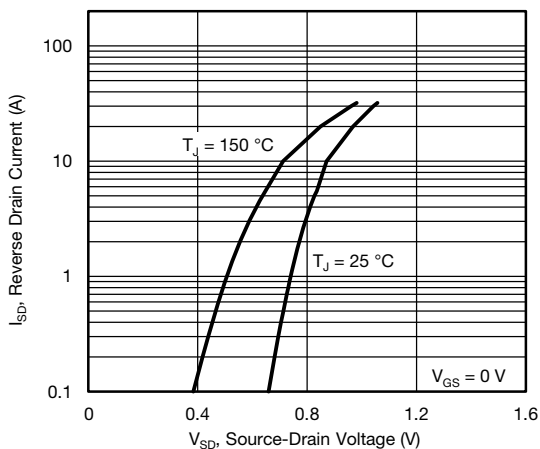
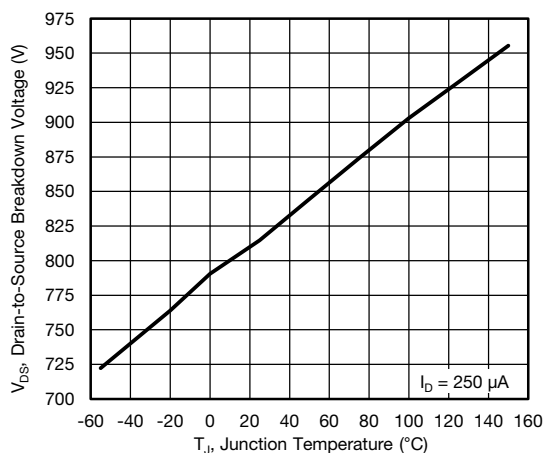
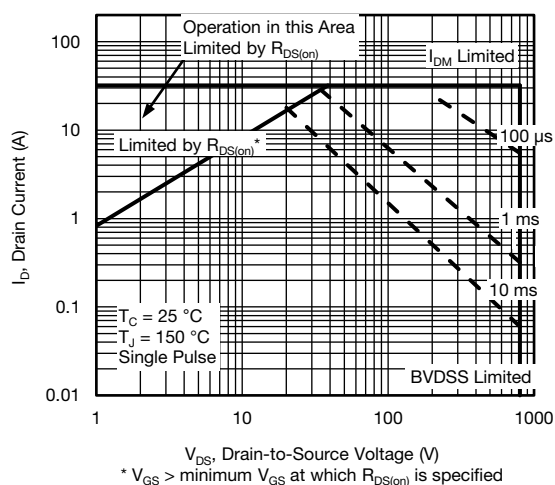
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

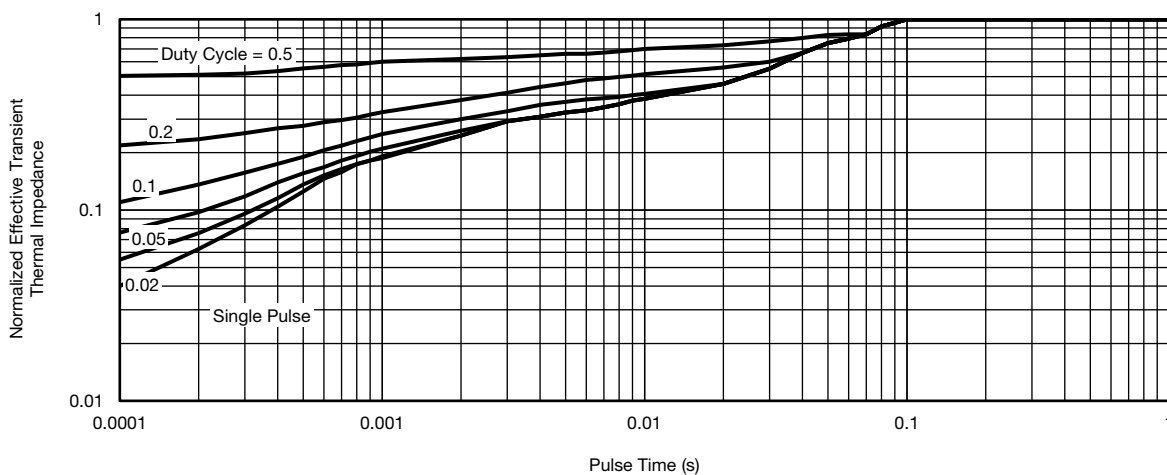
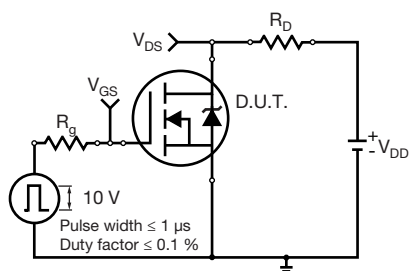
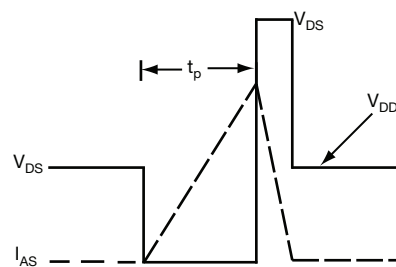
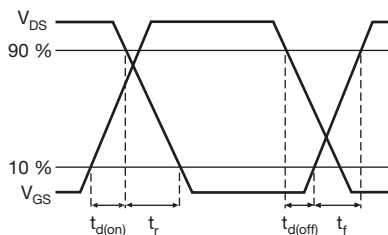
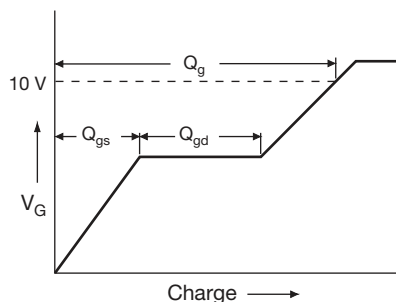
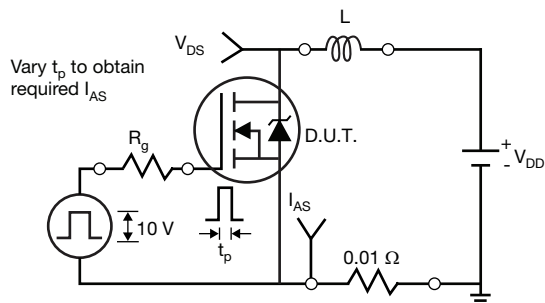
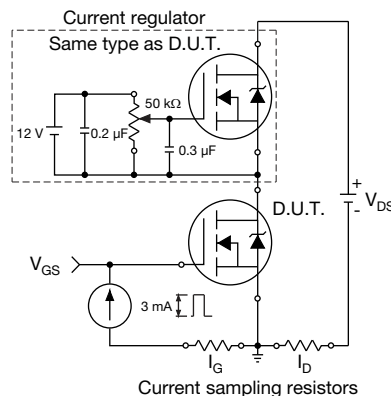
| PARAMETER                                                 | SYMBOL              | TEST CONDITIONS                                                                                                                                       | MIN. | TYP. | MAX.      | UNIT                  |
|-----------------------------------------------------------|---------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|-----------|-----------------------|
| <b>Static</b>                                             |                     |                                                                                                                                                       |      |      |           |                       |
| Drain-source breakdown voltage                            | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                | 800  | -    | -         | V                     |
| $V_{DS}$ temperature coefficient                          | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^{\circ}\text{C}$ , $I_D = 1\text{ mA}$                                                                                       | -    | 1.1  | -         | V/ $^{\circ}\text{C}$ |
| Gate-source threshold voltage (N)                         | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                    | 2    | -    | 4         | V                     |
| Gate-source leakage                                       | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$                                                                                                                            | -    | -    | $\pm 100$ | nA                    |
|                                                           |                     | $V_{GS} = \pm 30\text{ V}$                                                                                                                            | -    | -    | $\pm 1$   | $\mu\text{A}$         |
| Zero gate voltage drain current                           | $I_{DSS}$           | $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                                       | -    | -    | 1         | $\mu\text{A}$         |
|                                                           |                     | $V_{DS} = 640\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$                                                                 | -    | -    | 10        |                       |
| Drain-source on-state resistance                          | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$ , $I_D = 5.5\text{ A}$                                                                                                         | -    | 0.38 | 0.44      | $\Omega$              |
| Forward transconductance                                  | $g_{fs}$            | $V_{DS} = 30\text{ V}$ , $I_D = 5.5\text{ A}$                                                                                                         | -    | 4.5  | -         | S                     |
| <b>Dynamic</b>                                            |                     |                                                                                                                                                       |      |      |           |                       |
| Input capacitance                                         | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 100\text{ V}$ ,<br>$f = 1\text{ MHz}$                                                                            | -    | 1670 | -         | pF                    |
| Output capacitance                                        | $C_{oss}$           |                                                                                                                                                       | -    | 68   | -         |                       |
| Reverse transfer capacitance                              | $C_{rss}$           |                                                                                                                                                       | -    | 9    | -         |                       |
| Effective output capacitance, energy related <sup>a</sup> | $C_{o(er)}$         | $V_{DS} = 0\text{ V to } 480\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                        | -    | 43   | -         |                       |
| Effective output capacitance, time related <sup>b</sup>   | $C_{o(tr)}$         |                                                                                                                                                       | -    | 212  | -         |                       |
| Total gate charge                                         | $Q_g$               | $V_{GS} = 10\text{ V}$ , $I_D = 5.5\text{ A}$ , $V_{DS} = 480\text{ V}$                                                                               | -    | 44   | 88        | nC                    |
| Gate-source charge                                        | $Q_{gs}$            |                                                                                                                                                       | -    | 9    | -         |                       |
| Gate-drain charge                                         | $Q_{gd}$            |                                                                                                                                                       | -    | 16   | -         |                       |
| Turn-on delay time                                        | $t_{d(on)}$         | $V_{DD} = 480\text{ V}$ , $I_D = 5.5\text{ A}$ ,<br>$V_{GS} = 10\text{ V}$ , $R_g = 9.1\text{ }\Omega$                                                | -    | 18   | 36        | ns                    |
| Rise time                                                 | $t_r$               |                                                                                                                                                       | -    | 15   | 30        |                       |
| Turn-off delay time                                       | $t_{d(off)}$        |                                                                                                                                                       | -    | 55   | 110       |                       |
| Fall time                                                 | $t_f$               |                                                                                                                                                       | -    | 18   | 36        |                       |
| Gate input resistance                                     | $R_g$               | $f = 1\text{ MHz}$ , open drain                                                                                                                       | 0.4  | 0.9  | 1.8       | $\Omega$              |
| <b>Drain-Source Body Diode Characteristics</b>            |                     |                                                                                                                                                       |      |      |           |                       |
| Continuous source-drain diode current                     | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode  | -    | -    | 12        | A                     |
| Pulsed diode forward current                              | $I_{SM}$            |                                                                                                                                                       | -    | -    | 32        |                       |
| Diode forward voltage                                     | $V_{SD}$            | $T_J = 25\text{ }^{\circ}\text{C}$ , $I_S = 5.5\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                     | -    | -    | 1.2       | V                     |
| Reverse recovery time                                     | $t_{rr}$            | $T_J = 25\text{ }^{\circ}\text{C}$ , $I_F = I_S = 5.5\text{ A}$ ,<br>$di/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 25\text{ V}$                         | -    | 345  | 690       | ns                    |
| Reverse recovery charge                                   | $Q_{rr}$            |                                                                                                                                                       | -    | 4.2  | 8.4       | $\mu\text{C}$         |
| Reverse recovery current                                  | $I_{RRM}$           |                                                                                                                                                       | -    | 21   | -         | A                     |

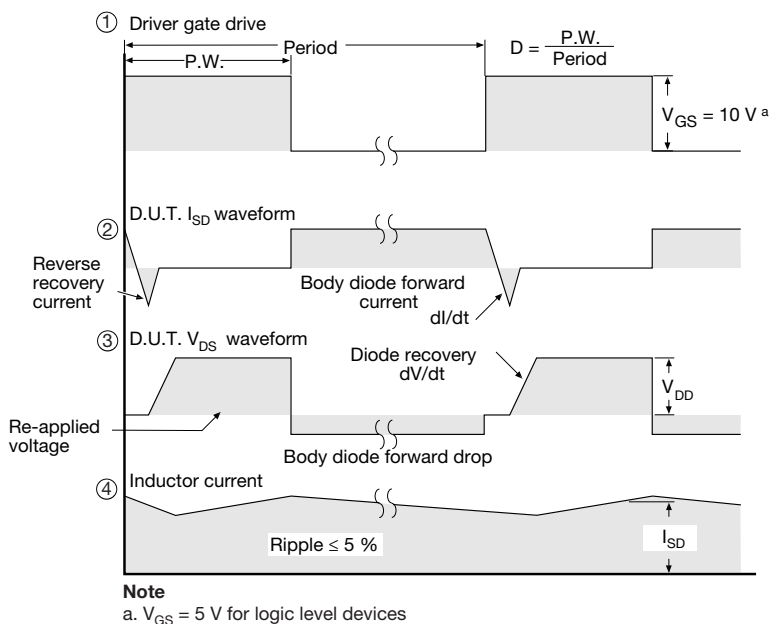
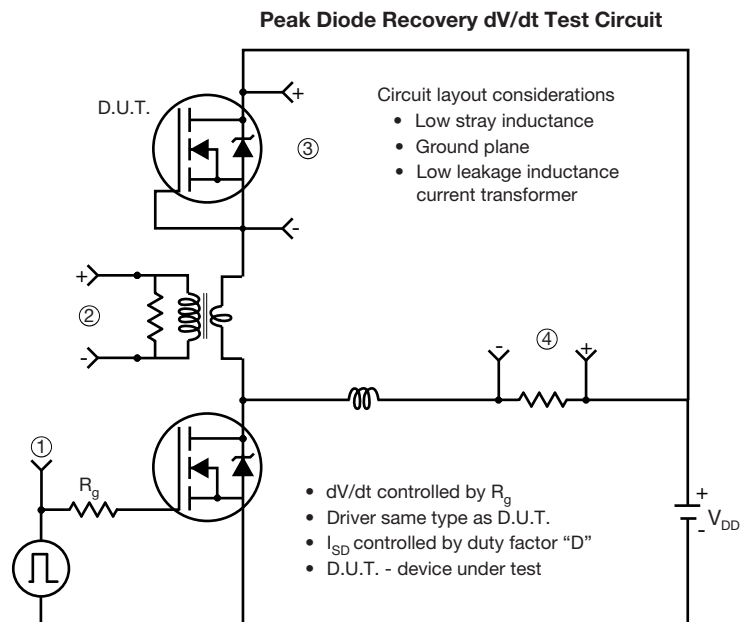
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$   
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**


**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 10 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

**Fig. 11 - Temperature vs. Drain-to-Source Voltage**

**Fig. 9 - Maximum Safe Operating Area**

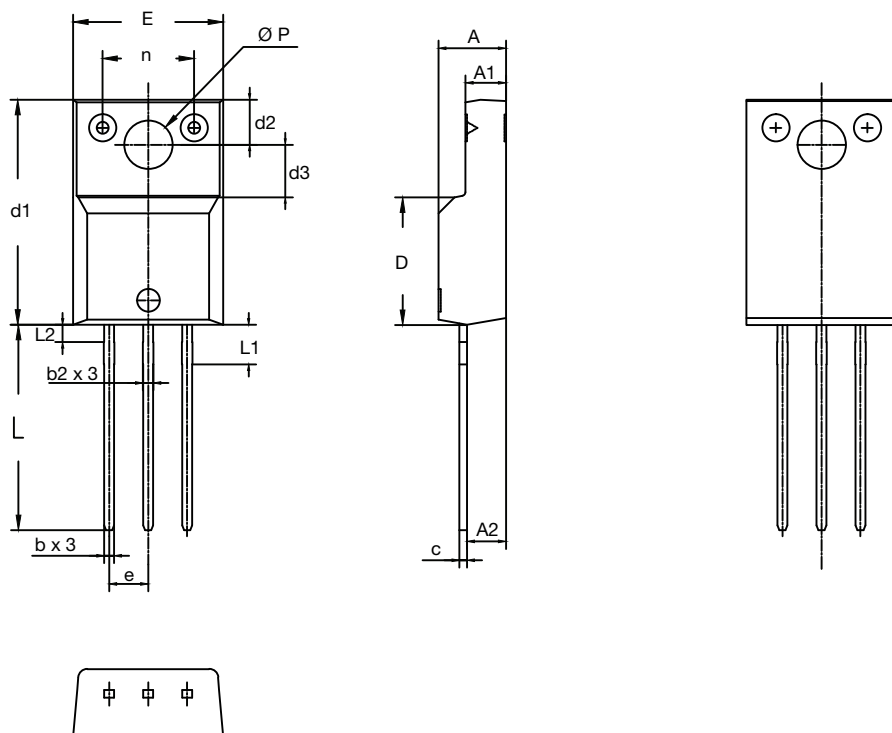

**Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case**

**Fig. 13 - Switching Time Test Circuit**

**Fig. 16 - Unclamped Inductive Waveforms**

**Fig. 14 - Switching Time Waveforms**

**Fig. 17 - Basic Gate Charge Waveform**

**Fig. 15 - Unclamped Inductive Test Circuit**

**Fig. 18 - Gate Charge Test Circuit**



**Fig. 19 - For N-Channel**

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## TO-220 FULLPAK Thin Lead



| SYMBOL | DIMENSIONS  |       |        |       |
|--------|-------------|-------|--------|-------|
|        | MILLIMETERS |       | INCHES |       |
|        | MIN.        | MAX.  | MIN.   | MAX.  |
| A      | 4.30        | 4.70  | 0.169  | 0.185 |
| A1     | 2.50        | 2.90  | 0.098  | 0.114 |
| A2     | 2.50        | 2.70  | 0.098  | 0.106 |
| b      | 0.60        | 0.80  | 0.024  | 0.031 |
| b2     | 0.60        | 0.90  | 0.024  | 0.035 |
| c      | -           | 0.60  | -      | 0.024 |
| D      | 8.30        | 8.70  | 0.327  | 0.342 |
| d1     | 14.70       | 15.30 | 0.579  | 0.602 |
| d2     | 2.90        | 3.10  | 0.114  | 0.122 |
| d3     | 3.40        | 3.60  | 0.134  | 0.142 |
| E      | 9.70        | 10.30 | 0.382  | 0.406 |
| e      | 2.50        | 2.70  | 0.098  | 0.106 |
| L      | 13.40       | 13.80 | 0.528  | 0.543 |
| L1     | 2.50        | 2.80  | 0.098  | 0.110 |
| L2     | -           | 1.20  | -      | 0.047 |
| n      | 6.05        | 6.15  | 0.238  | 0.242 |
| Ø P    | 3.00        | 3.40  | 0.118  | 0.134 |

ECN: T16-0549-Rev. C, 12-Sep-16  
DWG: 6021



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